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(P-46)	Conductive Particle Actuation Using Capacitive Force: A New Method to Measure Adhesion Force between Conductive Particles and Microelectrodes H. W. Yoon, K. H. Yang, M. Hong, <i>Korea Univ., Korea</i>	N/A
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Friday, July 7

Session 6 : Novel Fabrication Processing for Thin-Film Materials (9 : 15 ~ 10 : 40)

Chairpersons :	H. Ago, <i>Kyushu Univ., Japan</i> K. Matsuda, <i>Kyoto Univ., Japan</i>
9:15 (6-1)	Inhomogeneous Crystallization of Sputter-Deposited Amorphous Ge Films (Invited) R. Nakamura ¹ , M. Okugawa ¹ , M. Ishimaru ² , H. Yasuda ³ , H. Numakura ¹ , ¹ <i>Osaka Prefecture Univ., Japan</i> , ² <i>Kyushu Inst. of Technol., Japan</i> , ³ <i>Osaka Univ., Japan</i>276
9:40 (6-2)	Formation of Graphene-Related Organic Film by Hot Mesh Deposition Using W Mesh Supported Ni A. Heya ¹ , R. Yamasaki ² , N. Matsuo ¹ , ¹ <i>Univ. of Hyogo, Japan</i> , ² <i>Tocolo, Japan</i>279
10:00 (6-3)	Bimetal-Catalyzed VLS Growth of InGaZnO Nanowire from Amorphous Thin Film J. C. Felizco, M. Uenuma, D. Senaha, Y. Ishikawa, Y. Uraoka, <i>Nara Inst. of Sci. and Technol., Japan</i> ..283
10:20 (6-4)	Effect of Trichloroethene (TCE) on Deposition Rate and Film Quality of Low-Temperature SiO ₂ Films Grown Using Silicone Oil and Ozone Gas P. Jain, S. Horita, <i>Japan Advanced Inst. of Sci. and Technol., Japan</i> 285

— Coffee Break —

Session 7 : Novel Thin-Film Devices (11 : 00 ~ 12 : 00)

Chairpersons :	S. Sato, <i>Fujitsu Labs., Japan</i> M. Kimura, <i>Ryukoku Univ., Japan</i>
11:00 (7-1)	Improved Characteristics of Polymer Photodetectors Using Phosphonic Acid-Based Self-Assembled Monolayer Treatment for Interfacial-Engineering of Ga-Doped ZnO Electrodes H. Kajii, Y. Mohri, H. Okui, M. Kondow, Y. Ohmori, <i>Osaka Univ., Japan</i>288
11:20 (7-2)	Ultralow Temperature Solution Processed Gate Dielectrics Using Molecular Structured Precursors and Highly Energetic Photochemical Process J. -W. Jo ¹ , M. -G. Kim ¹ , J. Park ¹ , J. S. Heo ¹ , J. -G. Kang ¹ , S. -G. Ban ¹ , Y. -H. Kim ² , S. Hwang ³ , J. Kim ⁴ , S. K. Park ¹ , ¹ <i>Chung-Ang Univ., Korea</i> , ² <i>Sungkyunkwan Univ., Korea</i> , ³ <i>Korea Univ., Korea</i> , ⁴ <i>Hanyang Univ., Korea</i>292
11:40 (7-3)	A Transimpedance Amplifier Based on a LTPS Process Operated in Alkali Vapor J. Schmidt, P. Schalberger, H. Baur, R. Löw, T. Pfau, H. Kübler, N. Frühauf, <i>Univ. of Stuttgart, Germany</i>296

— Lunch —

Session 8 : Advanced Materials for TFT (14: 00 ~ 15 : 05)

Chairpersons :	D. Tu, <i>Linköping Univ., Sweden</i> Y. Terai, <i>JOLED, Japan</i>
14:00 (8-1)	Material Design of Ultra-Wide Bandgap AOSs and their Applications in Photostable Electronic Devices (Invited) J. Kim ^{1,3} , N. Nakamura ^{2,3} , T. Kamiya ¹ , H. Hosono ^{1,3} , ¹ <i>Tokyo Inst. of Technol., Japan</i> , ² <i>Asahi Glass, Japan</i> , ³ <i>Japan Sci. and Technol. Agency, Japan</i> 299
14:25 (8-2)	Development of Inkjet Printed N-Type Organic Field-Effect Transistor with Morphology Control of Insulating Layer S. J. Moon ^{1,2} , M. Robin ¹ , K. Wenlin ¹ , T. M. -Brahim ¹ , E. Jacques ¹ , M. Harnois ¹ , B. S. Bae ² , ¹ <i>Univ. Rennes 1, France</i> , ² <i>Hoseo Univ., Korea</i> 302
14:45 (8-3)	Instant Glue Passivation Layer of Indium-Gallium-Zinc Oxide Thin Film Transistors H. Yoo, Y. J. Tak, B. H. Kang, H. J. Kim, <i>Yonsei Univ., Korea</i> 306

— Coffee Break —

Session 9 : Novel TFT Technologies for High Performance Device (15 : 20 ~ 16 : 25)

Chairpersons :	N. -S. Roh, <i>Samsung Electronics, Korea</i> S. Horita, <i>JAIST, Japan</i>	
15:20 (9-1)	High Mobility Oxide TFT for OLED Pixel Circuits (Invited) J. U. Bae, J. H. Baeck, P. Yun, D. H. Kim, Y. H. Jang, K. -S. Park, S. Y. Yoon, I. B. Kang, <i>LG Display, Korea</i>	309
15:45 (9-2)	Transparent Oxide Thin-Film Transistors with Vertical Channel Structure Using Atomic-Layer- Deposited In-Ga-Zn-O Thin Films Y. -M. Kim ¹ , G. -H. Kim ² , S. -M. Yoon ¹ , ¹ <i>Kyung Hee Univ., Korea</i> , ² <i>Electronics &</i> <i>Telecommunication Res. Inst., Korea</i>	312
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Author Interviews (16 : 30 ~ 17 : 00)